



SiC detectors for neutron monitoring

C. Manfredotti^{a,b,*}, A. Lo Giudice^a, F. Fasolo^{a,b}, E. Vittone^{a,b}, C. Paolini^a,
F. Fizzotti^a, A. Zanini^b, G. Wagner^c, C. Lanzieri^d

^aExperimental Physics Department, University of Torino, Via Giuria 1, 10125 Torino, Italy

^bINFN Sez. Torino, Via Giuria 1, 10125 Torino, Italy

^cInstitut fuer KristallZuechtung, IKZ, Berlin, Germany

^dAMSJV, Alenia, Rome, Italy

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Abstract

Semiconductor detectors equipped with a converter like ${}^6\text{LiF}$ or ${}^{10}\text{B}$ can currently be considered a very interesting alternative to conventional neutron detectors, especially because of their compactness and reliability. The materials for the detection of the ions produced in the converter are generally either Si or GaAs. SiC detectors presented in this work are completely new devices which are proved to be very suitable for neutron detection, dosimetry and beam monitoring. Their capability to withstand high radiation doses should largely overcome the performances of Si and GaAs; moreover, because of the lower Z value, gamma-ray discrimination turns out to be more efficient. In this work, the results obtained with a series of large-area epitaxial SiC Schottky barrier detectors will be presented and discussed.

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1. Introduction

In recent years there has been an increasing demand for new types of neutron detectors and dosimeters, to be used in applications such as

detection of nuclear weapons, fissile materials or drugs inspections at customs and airports, boron neutron capture therapy (BNCT), etc. For these applications it is necessary to dispose off small, portable and reliable neutron detectors.

Semiconductor detectors [1–4] exhibit remarkable advantages: they are small, simple and can work at low bias voltages or even in the photo-voltaic mode. Other characteristics are advisable: a good discrimination ability against gamma

*Corresponding author. Experimental Physics Department, University of Torino, Via Giuria 1, 10125 Torino, Italy. Tel.: +39 011 6707306; fax: +39 011 6691104.

E-mail address: manfredotti@to.infn.it (C. Manfredotti).